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Vishay Siliconix

TO-263

D G

Top View

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.00175			
$R_{DS(on)}$ max. (Ω) at V_{GS} = 7.5 V	0.00220			
Q _g typ. (nC)	141			
I _D (A)	150 ^d			
Configuration	Single			

FEATURES

N-Channel 60 V (D-S) MOSFET

- TrenchFET[®] power MOSFET
- Maximum 175 °C junction temperature
- Very low Q_{gd} reduces power loss from passing through $V_{plateau}$
- 100 % $\rm R_g$ and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Power supply
 Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management
- OR-ing / e-fuse

N-Channel MOSFET

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ORDERING INFORMATION		
Package	TO-263	
Lead (Pb)-free and halogen-free	SUM50010E-GE3	

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	60	v
Gate-source voltage		V _{GS}	± 20	V
Continuous drain current (T _J = 150 °C)	T _C = 25 °C	1	150 ^d	
	T _C = 70 °C	I _D	150 ^d	A
Pulsed drain current (t = 100 µs)		I _{DM}	500	A
Avalanche current		I _{AS}	60	
Single avalanche energy ^a	L = 0.1 mH	E _{AS}	180	mJ
Maximum power dissinction a	T _C = 25 °C	D-	375 ^b	w
Maximum power dissipation ^a	T _C = 125 °C	P _D	125 ^b	v
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient (PCB mount) ^c	R _{thJA}	40	°C/W	
Junction-to-case (drain)	R _{thJC}	0.4	0/10	

Notes

a. Duty cycle ≤ 1 %

b. See SOA curve for voltage derating

c. When mounted on 1" square PCB (FR4 material)

d. Package limited

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RoHS COMPLIANT

HALOGEN

FREE

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					1	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	60	-	-	.,
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	-	4	V
Gate-body leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 250	nA
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1	μA
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	150	
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	5	mA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10$ V, $V_{GS} = 10$ V	120	-	-	Α
		$V_{GS} = 10 \text{ V}, I_{D} = 30 \text{ A}$	-	0.00145	0.00175	-
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.00183	0.00220	Ω
Forward transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 30 \text{ A}$	-	120	-	S
Dynamic ^b			1		II	
Input capacitance	C _{iss}		-	10 895	-	
Output capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 30 V, f = 1 MHz	-	2420	-	pF
Reverse transfer capacitance	C _{rss}		-	85	-	
Total gate charge ^c	Qg		-	141	212	
Gate-source charge ^c	Q _{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 20 A	-	43.6	-	-
Gate-drain charge ^c	Q _{gd}		-	19.1	-	nC
Output charge	Q _{oss}	$V_{DS} = 50 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	143	215	
Gate resistance	R _g	f = 1 MHz	0.24	1.2	2.4	Ω
Turn-on delay time ^c	t _{d(on)}		-	28	56	
Rise time ^c	tr	$V_{DD} = 30 \text{ V}, \text{ R}_{\text{I}} = 3 \Omega$	-	12	24	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	50	100	ns
Fall time ^c	t _f		-	13	26	
Drain-Source Body Diode Ratings	and Characte	ristics ^b (T _C = 25 °C)				
Pulsed current (t = 100 µs)	I _{SM}		-	-	250	А
Forward voltage ^a	V _{SD}	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.8	1.5	V
Reverse recovery time	t _{rr}		-	75	150	ns
Peak reverse recovery charge	I _{RM(REC)}		-	2.8	5.6	А
Reverse recovery charge	Q _{rr}	$I_F = 34$ A, di/dt = 100 A/µs	-	0.12	0.24	μC
Reverse recovery fall time	ta		-	38	-	20
Reverse recovery rise time	t _b		-	37	-	ns

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

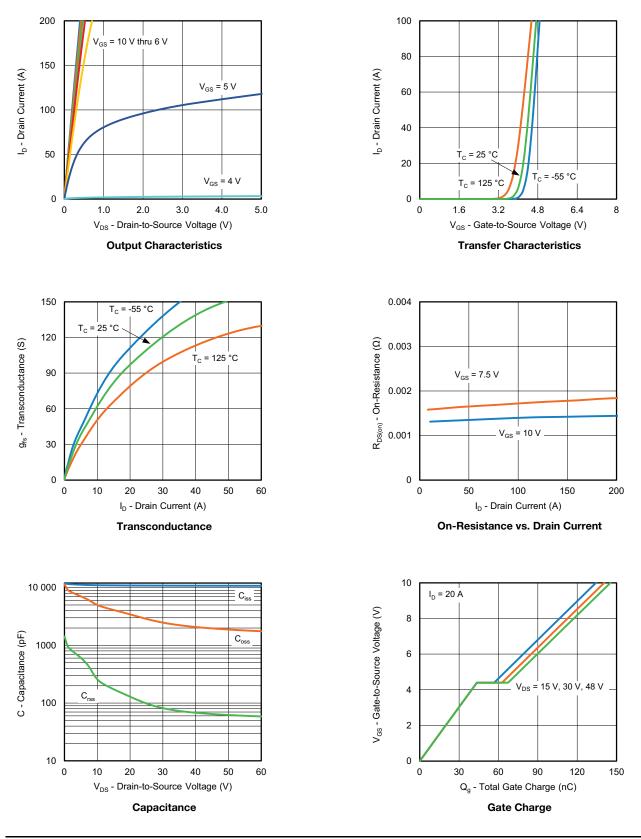
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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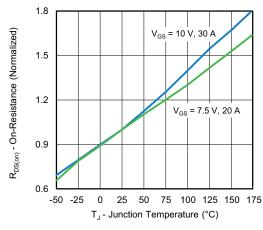
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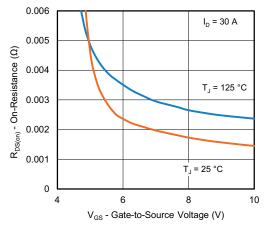


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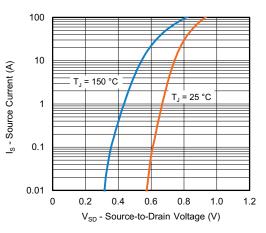
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



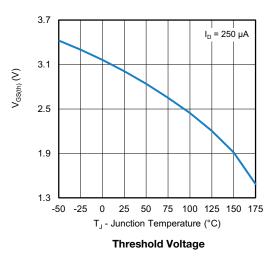
On-Resistance vs. Junction Temperature

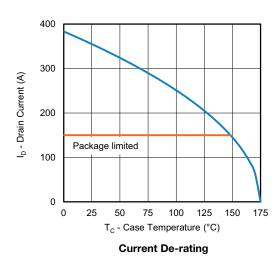


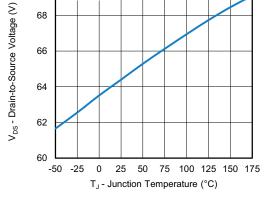
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

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 $I_{D} = 250 \ \mu A$

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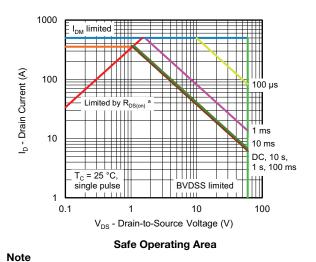
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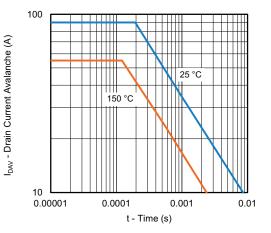
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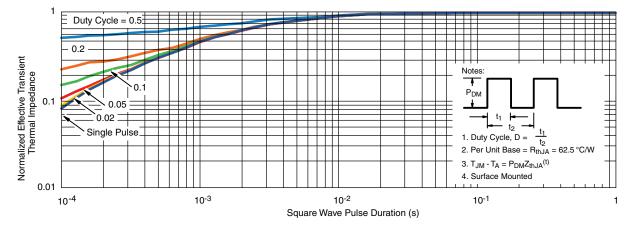
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)





Single Pulse Avalanche Current Capability vs. Time

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual pplication parameters and operating conditions

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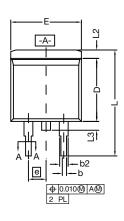
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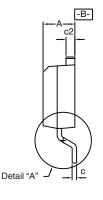


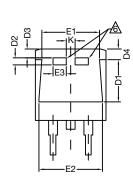
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TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

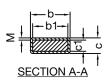








DETAIL A (ROTATED 90°)



		INCHES		MILLIN	IETERS	
DIM.		MIN.	MAX.	MIN.	MAX.	
	А	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
е		0.100 BSC		2.54 BSC		
К		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		L3 0.050		1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
- Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

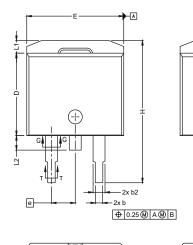
This feature is for thick lead.

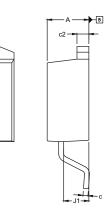
Revison: 28-Oct-2024

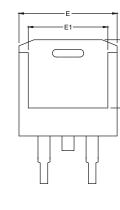


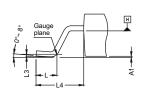
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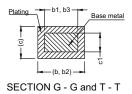
VERSION 2: FACILITY CODE = N











OPTION 1 2 leads



2

 \oplus

3 leads

DIM.	MIN.	MAX.
A	4.36	4.56
A1	0	0.25
b	0.70	0.90
b1	0.51	0.89
b2	1.20	1.46
b3	1.17	1.37
с	0.38	0.694
c1	0.38	0.534
c2	1.19	1.34
D	8.60	9.00
D1	6.9	7.5
E	10.15	10.55
E1	8.1	8.7
e	2.5	4 BSC
Н	15.0	15.6
L	1.9	2.5
L1	-	1.65
L2	-	1.78
L3	0.25 typ.	
L4	4.78 5.28	
J1	2.56	2.96
ECN: S24-1080-Rev. L, 28-Oct-2024 DWG: 5843		



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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